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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



MS2441

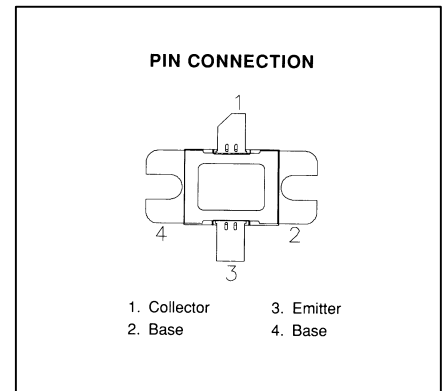
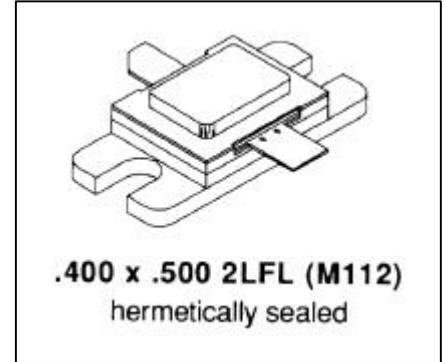
RF & MICROWAVE TRANSISTORS L-BAND AVIONICS APPLICATIONS

Features

- DESIGNED FOR HIGH POWER PULSED IFF AND DME APPLICATIONS
- 400 W (min.) DME 1025 – 1150 MHz
- 1025 – 1150 MHz
- 50 VOLTS
- $P_{OUT} = 400$ WATTS
- $G_P = 6.5$ dB MINIMUM
- 20:1 VSWR CAPABILITY
- INPUT/OUTPUT MATCHING
- COMMON BASE CONFIGURATION

DESCRIPTION:

The MS2441 is a silicon NPN power transistor designed for high peak power and low duty cycles applications such as DME and IFF. The MS2441 utilizes internal input/output impedance matching, resulting in improved broadband performance and a low thermal resistance.



ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	65	V
V_{CES}	Collector-Emitter Voltage	65	V
V_{EBO}	Emitter-Base Voltage	3.5	V
I_C	Device Current	22	A
P_{DISS}	Power Dissipation	1458	W
T_J	Junction Temperature	+200	$^{\circ}C$
T_{STG}	Storage Temperature	-65 to +150	$^{\circ}C$

Thermal Data

$R_{TH(J-C)}$	Junction-case Thermal Resistance	0.12	$^{\circ}C/W$
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MS2441

ELECTRICAL SPECIFICATIONS (Tcase = 25 °C)

STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CBO}	$I_C = 25mA$	$I_E = 0mA$	65	---	---	V
BV_{CES}	$I_C = 50mA$	$V_{BE} = 0mA$	65	---	---	V
BV_{EBO}	$I_E = 10mA$	$I_C = 0mA$	3.5	---	---	V
I_{CES}	$V_{CE} = 50V$	$I_E = 0mA$	---	---	25	mA
h_{FE}	$V_{CE} = 5V$	$I_C = .25A$	5	---	200	---

DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	$f = 1025 - 1150MHz$	$P_{IN} = 90W$	$V_{CC} = 50V$	400	---	---	W
G_p	$f = 1025 - 1150MHz$	$P_{IN} = 90W$	$V_{CC} = 50V$	6.5	---	---	dB

Conditions: Pulse Width = 10μS Duty Cycle = 1%

This device is suitable for use under other pulse width/duty cycle conditions.
Please contact the factory for specific applications assistance.

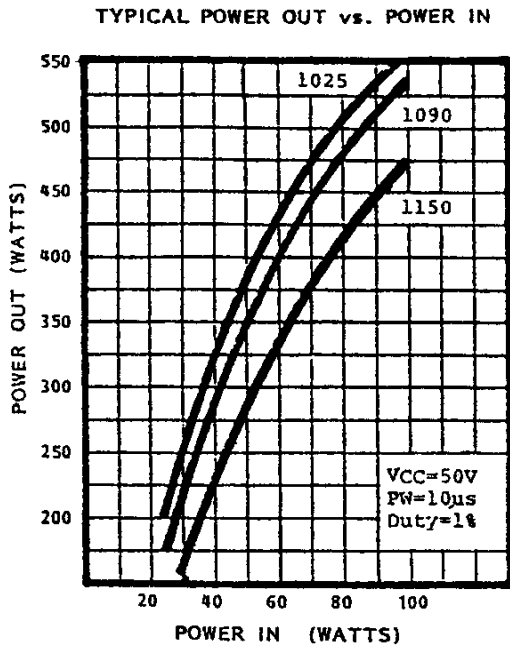
IMPEDANCE DATA:

FREQ	$Z_{IN}(\Omega)$	$Z_{CL}(\Omega)$
1020 MHz	2.89 + j4.1	1.38 – j3.2
1090 MHz	2.32 + j3.4	1.33 – j2.8
1150 MHz	1.99 + j2.8	1.26 – j2.5

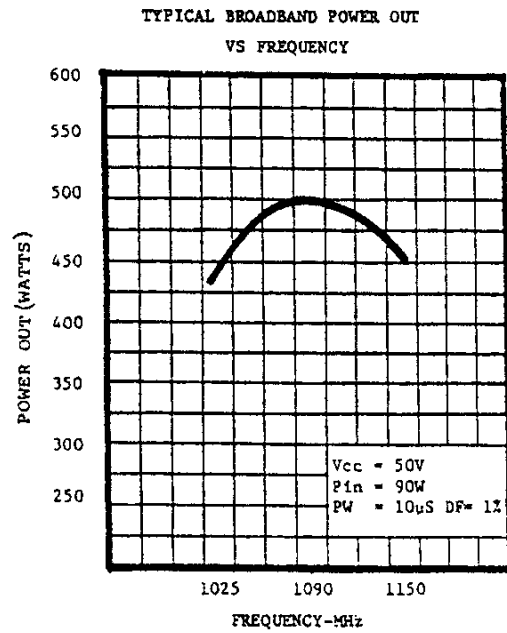
$P_{IN} = 90 W$
 $V_{CE} = 50 V$

TYPICAL PERFORMANCE

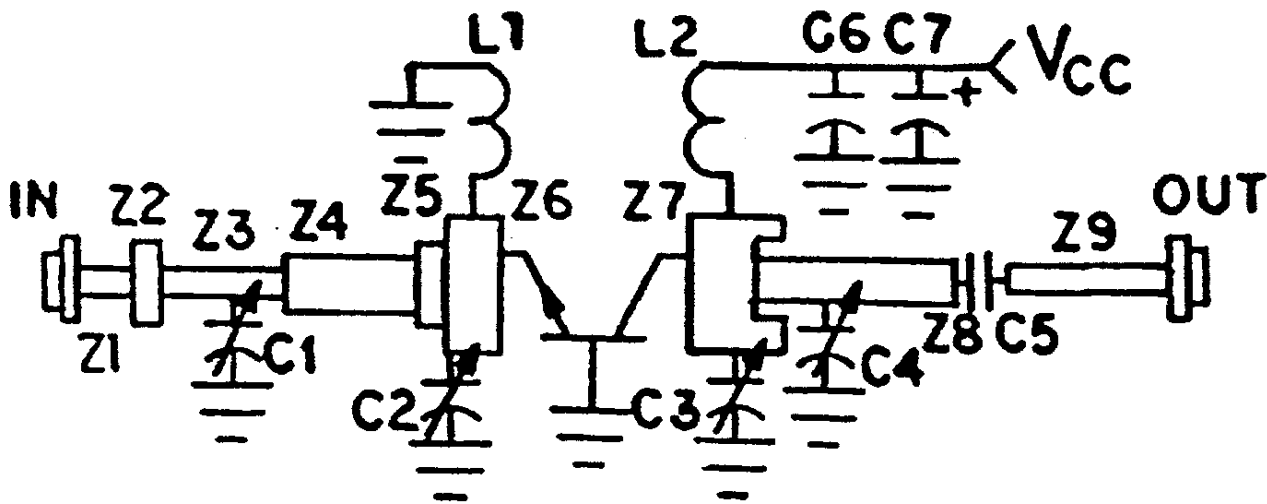
POWER OUTPUT vs POWER INPUT



POWER OUTPUT vs FREQUENCY



TEST CIRCUIT



All Dimensions in Inches Unless Otherwise specified

C1 : 0.4 - 2.5pF Johanson Gigatrim
C2, C3,
C4 : 0.6 - 4.5pF Johanson Gigatrim
C5 : 82pF Chip Capacitor, .055 Sq.

L1 : Loop, #18 Tinned, .36 Wide x .27 above Circuit
L2 : 4 3/4 Turns, #24 En., C.W., .075 I.D.

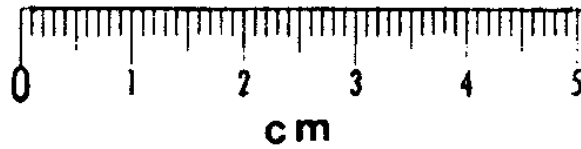
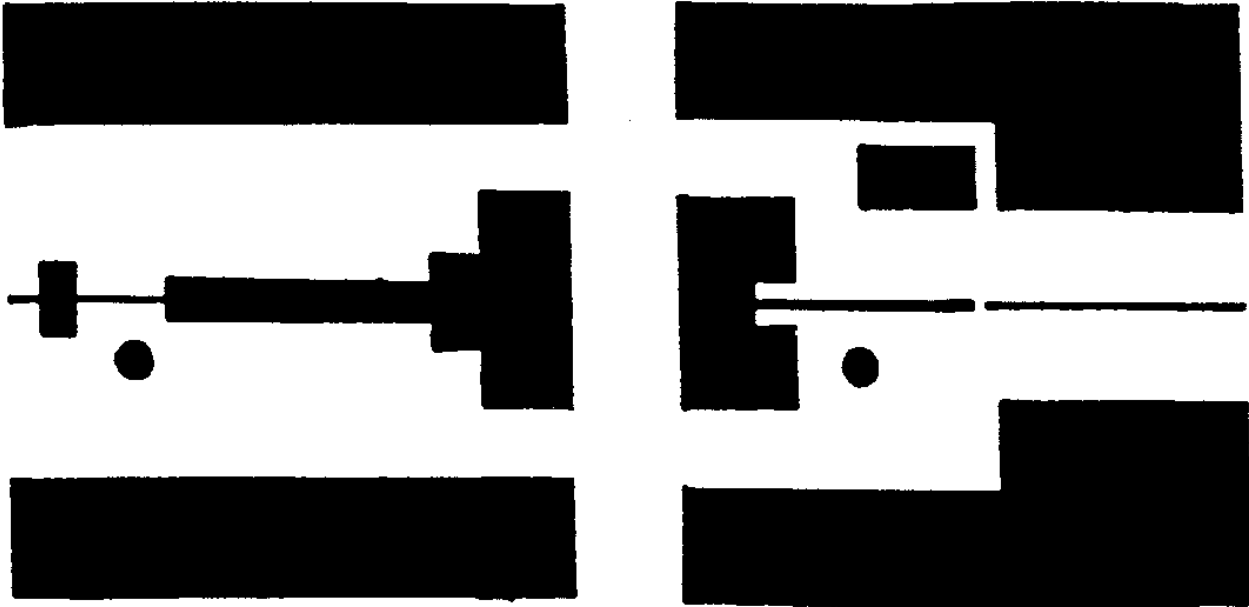
Z1 : 50Ω(.02 Wide)
Z2 : .250 x .120

Z3 : 50Ω .020 x .330; C1 tapped .15 from Load
Z4 : .145 x .920
Z5 : .325 x .180
Z6 : .730 x .315
Z7 : .710 x .425 with .140 x .150 cutout
Z8 : .35 x .780; C4 Tapped .36 from Cen
Z9 : 50Ω

C1, C4 : Cold End Terminated Through Eyelet.

PC BOARD LAYOUT

3M EPSILAM 10, .032 THK., 10Z.



PACKAGE MECHANICAL DATA

